

700V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

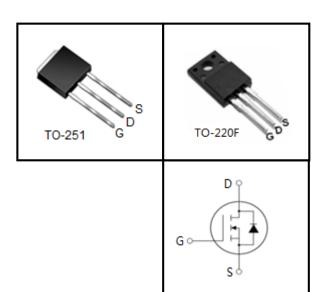
APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	Package	Marking		
CS1N70SU	TO-251	CS1N70SU		
CS1N70SF	TO-220F	CS1N70SF		

Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
Parameter	Symbol	Val	Unit		
Tarameter		TO-220F	TO-251		
Drain-Source Voltage ($V_{GS} = 0V$)	V _{DSS}	700		V	
Continuous Drain Current	I _D	1		A	
Pulsed Drain Current (note1)	I _{DM}	3.6		A	
Gate-Source Voltage	V _{GSS}	±:	30	V	
Single Pulse Avalanche Energy (note2)	E _{AS}	4.05		mJ	
Avalanche Current (note1)	I _{AR}	0.9		A	
Repetitive Avalanche Energy (note1)	E _{AR}	2.43		mJ	
Power Dissipation ($T_c = 25^{\circ}C$)	P _D	1'	7	w	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C	

Thermal Resistance				
Parameter	Symbol	Va	l lmit	
		TO-220F	TO-251	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	7.3		°C/W
Thermal Resistance, Junction-to-Ambient	R _{thJA}	60		



CS1N70SU, CS1N70SF



Specifications $T_J = 25^{\circ}C$, unless otherwise noted								
Parameter	Symbol	Toot Conditions	Value			Unit		
		Test Conditions	Min.	Тур.	Max.	Unit		
Static			_	_				
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250 \mu A$	700			V		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 700V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA		
Gate-Source Leakage	I _{GSS}	V_{GS} = $\pm 30V$			±100	nA		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		4.2	V		
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_{D} = 0.45A$		12.7	14	Ω		
Dynamic								
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V,		122		рF		
Output Capacitance	C _{oss}			11				
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		1				
Total Gate Charge	Q _g	V _{DD} = 560V, I _D = 1A, V _{GS} = 15V		5.7		uC		
Gate-Source Charge	Q _{gs}			0.8				
Gate-Drain Charge	Q _{gd}			3.5				
Turn-on Delay Time	t _{d(on)}			34		ns		
Turn-on Rise Time	t _r	$V_{\rm DD} = 350 \text{V}, \text{ I}_{\rm D} = 1\text{A}, \\ \text{R}_{\rm G} = 25 \ \Omega$		9				
Turn-off Delay Time	t _{d(off)}			42				
Turn-off Fall Time	t _f			32				
Drain-Source Body Diode Character	istics							
Continuous Body Diode Current	۱ _s	T 05.00			0.9	А		
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			3.6			
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C, I_{SD} = 0.45A, V_{GS} = 0V$			1.4	V		
Reverse Recovery Time	t _{rr}	V _{GS} = 0V,I _S = 1A,		539		ns		
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /µs		0.23		μC		

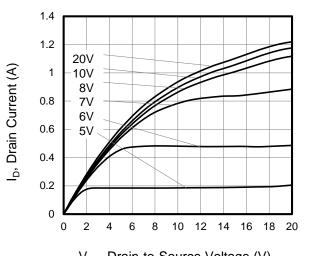
Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 °C
- 3. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%



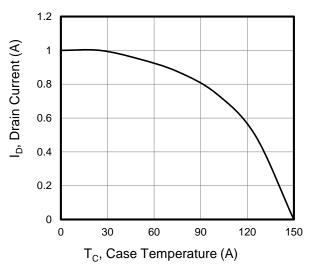
Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

Figure 1. Output Characteristics (T_J = 25°C)

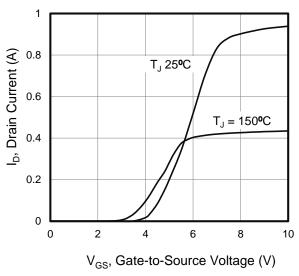


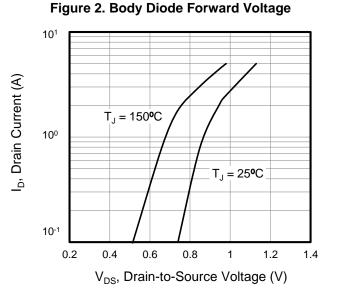
 V_{DS} , Drain-to-Source Voltage (V)



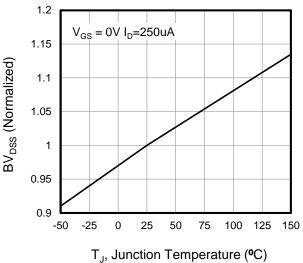


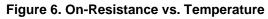


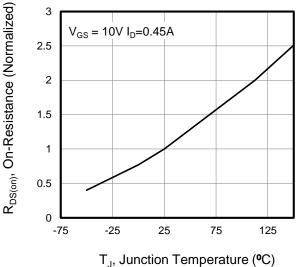






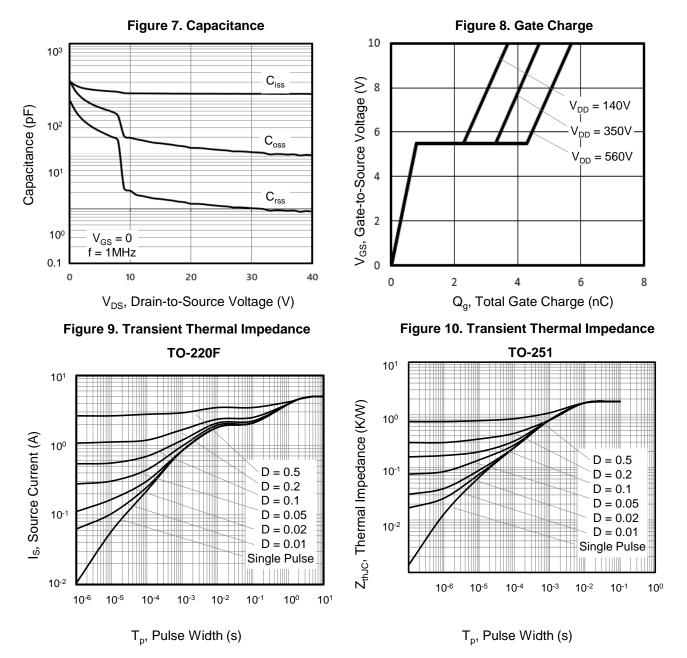








Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted







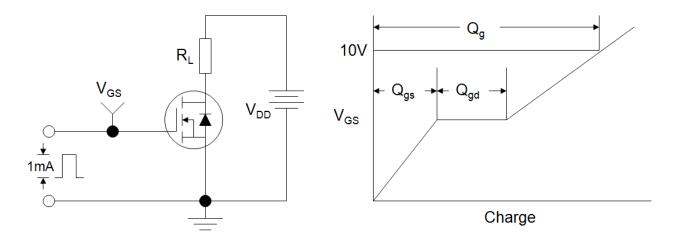


Figure B: Resistive Switching Test Circuit and Waveform

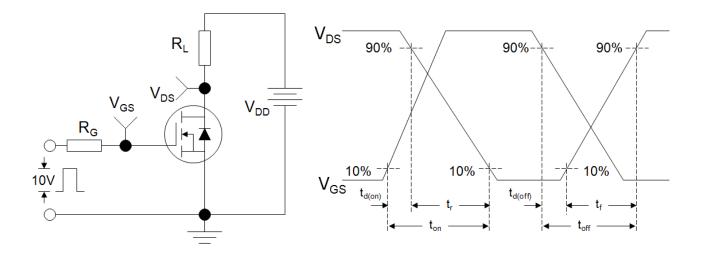
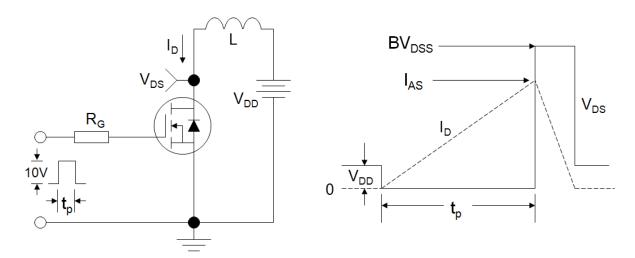
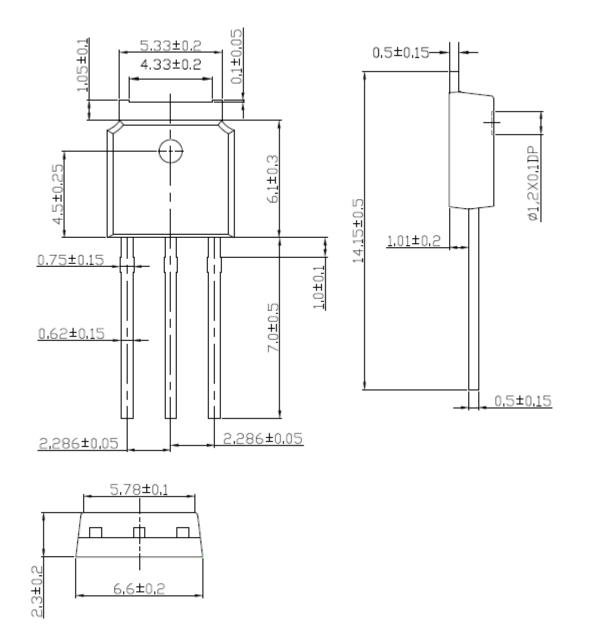


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



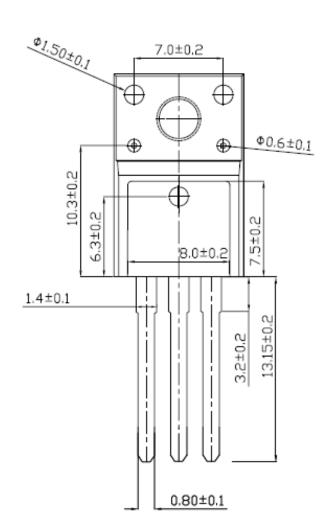


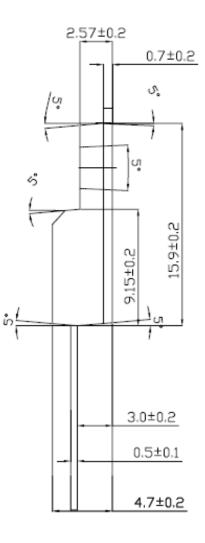


TO-251



TO-220F







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